

IN THE CLAIMS:

The claims pending in the instant application stand as follows:

Claims 1-14 (Cancelled).

Claim 15 (Previously Presented): A semiconductor device comprising:

a first wiring layer composed of a plurality of wiring patterns separate from each other embedded on a first insulating layer which covers a surface of a semiconductor substrate;

a nonconductive layer contacting and covering the first insulating layer and contacting the first wiring layer, a top of the first wiring layer not higher than a top of the first insulating layer, further wherein thickness of said nonconductive layer being arranged above the wiring layer is thicker than that of being arranged above the insulating layer.

Claim 16 (Previously Presented): A semiconductor device, comprising:

a substrate;

a first insulating layer covering a surface of the substrate;

a first wiring layer including a plurality of wiring patterns separate from each other embedded on an upper surface of the first insulating layer, the first wiring layer including a first material; and

a nonconductive layer contacting the first wiring layer, and contacting and covering the first insulating layer,

wherein a top of the first wiring layer is not higher than a top of the first insulating layer, and a thickness of said nonconductive layer being arranged above the wiring layer is thicker than that of being arranged above the insulating layer.

Claim 17 (Previously Presented): A semiconductor device, comprising:

a substrate;

a first insulating layer covering a surface of the substrate;

a first wiring layer including a plurality of wiring patterns separate from each other embedded on an upper surface of the first insulating layer; and

a nonconductive layer contacting the first wiring layer, and contacting and covering the first insulating layer, the nonconductive layer includes oxygen ions,

wherein a top of the first wiring layer is not higher than a top of the first insulating layer, and a thickness of said nonconductive layer being arranged above the wiring layer is thicker than that of being arranged above the insulating layer.

Claim 18 (Withdrawn): A semiconductor device, comprising:

a substrate,

a first insulating layer covering a surface of the substrate;

a first wiring layer including a plurality of wiring patterns separate from each other and embedded on an upper surface of the first insulating layer; and

a nonconductive layer that includes oxygen ions contacting the first wiring layer, and contacting and covering the first insulating layer,

wherein at least one of the wiring patterns includes at least one capacitor formed therein.